



FORM PTO-1449 (Modified) LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT		ATTY. DOCKET NO.: V0077/7117	SERIAL NO.: 09/602,059
		APPLICANT: Charles McKenna et al	
		FILING DATE: June 23, 2000	GROUP: 2881

#### U.S. PATENT DOCUMENTS

Exam Init	Ref Des	Document No.	Date	Name	Class	Sub Class	FILING DATE If Appropriate
UM.E.		4,276,477	6/81	Enge	250	398	
UM.E.		4,283,631	8/81	Turner	250	492B	
UM.E.		4,899,059	2/90	Freytsis et al	250	492.2	
UM.E.		4,922,106	5/90	Berrian et al	250	492.2	
UM.E.		5,350,926	9/94	White et al	250	492.21	
UM.E.		3,908,183	9/75	Ennis, Jr.	357	65	
UM.E.		4,011,449	3/77	Ko et al	250	492.21	
UM.E.		5,126,575	6/92	White	250	492.3	
UM.E.		5,343,047	8/94	Ono et al	250	251	
UM.E.		5,393,985	2/95	Yamakage et al	250	492.21	
UM.E.		5,399,871	3/95	Ito et al	250	251	
UM.E.		5,747,936	5/98	Harrison et al	250	492.21	
UM.E.		5,767,522	6/98	Kodama	250	398	
UM.E.		5,932,882	8/99	England et al	250	492.21	
UM.E.		5,969,366	10/99	England et al	250	492.21	
UM.E.		5,177,366	1/93	King et al	250	492.2	
UM.E.		5,091,655	2/92	Dykstra	250	492.2	

#### FOREIGN PATENT DOCUMENTS

	Country & Doc. No. (11)	Pub. Date (43)		Class	Sub Class	Translation Yes	No
UM.E.	EP 0 451 907	10/91					
UM.E.	EP 0 685 872	12/95					

#### OTHER ART

(Including Author, Title, Date, Pertinent Pages, Publication, Etc.)

UM.E.			S.N. Hong et al, "Formation of Ultrashallow P+ -n Junctions by Low-Energy Boron Implantation Using a Modified Ion Implanter, " Appl. Phys. Lett. 53(18), 31 Oct. 1988, pp. 1741-1743.
			A. Kluge et al, "A Flexible Target Chamber for a Varian 350 DF Implanter," Nuclear Inst. & Methods in Physics Research B37/38 (1989) pp. 584-587.
UM.E.			T. Kawai et al, "Nissin EXCEED 2000 - A New High Performance Medium Current Implanter", Ion Implantation Tech. 94, S. Coffa et al (eds.), 1995 Elsevier Science Publ. B.V., pp. 470-473.
			H. Glavish et al, "Fast Magnetic Scanning and Ion Optical Features of the New Ibis Oxygen Implanter", Ion Implantation Tech., D.F. Downey et al (eds.), 1993 Elsevier Science Publ. B.V., pp. 397-400.
UM.E.			A. Ray et al, "Overview of the Eaton NV-8200p High Beam Purity, Parallel Scanning Implanter", Ion Implantation Technology - 92, D. F. Downey et al (eds.), 1993 Elsevier Science Publ. B. V., pp. 401-404.

EXAMINER

Um. El-Shammaa

DATE CONSIDERED

10.31.02

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.